



Atty.  
Dkt. No.

M#

Client Ref.

276665

F01-243-USDIV

# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Applicant: MANABE

Appln. No.: 09/783,035

Filing Date: February 15, 2001

Date: June 11, 2002

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of

1

Examiner: Not Assigned

Group Art Unit: 2826

## U.S. PATENT DOCUMENTS

Examiner's Initials*		Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR						
	BR						
	CR						
	DR						
	ER						
	FR						
	GR						
	HR						
	IR						
	JR						
	KR						
	LR						

## FOREIGN PATENT DOCUMENTS

		Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
						Enclosed	No	Enclose	No
Kc	MR	58-102865	12/1984	JAPAN	MAEBOTOKE et al.	x			
Kc	NR	06-209120	07/1994	JAPAN	NAKAMURA et al.	x			
	OR								
	PR								
	QR								
	RR								
	SR								
	TR								
	UR								
	VR								

## OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

	WR								
	XR								
	YR								
	ZR								
	AAR								
	BBR								

Examiner

K Chutana

Date Considered:

6/16/2002

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

Atty.  
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F99-156-USDIV

INFORMATION DISCLOSURE STATEMENT  
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Applicant: MANABE et al.

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Examiner: M. Tran

Group Art Unit: 2811

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Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
KC	AR 5,281,830	01/1994	KOTAKI et al.	—	—	
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KC	DR 5,408,120	04/1995	MANABE et al.	—	—	
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						Enclosed	No	Enclose	No
KC	FR	599224	06/1994	EUROPE	NAKAMURA				
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KC	SR	Nakamura et al., "P-GaN/N-InGaN/N-GaN Double-Heterostructure Blue-Light-Emitting Diodes", Japanese J of Applied Physics, January 1993, Vol. 32, No. 1A/B, Part 2, pp. L8-L11.							
KC	TR	Nakamura et al., "Candela-class high-brightness InGaN/A1GaN double-heterostructure blue-light-emitting diodes", Applied Physics Letters, March 1994, Vol. 64, No. 13, pp. 1687-1689.							
KC	UR	Nakamura et al., "High-Brightness InGaN/A1GaN double-heterostructure blue-green-light-emitting diodes," J. of Applied Physics, December 1994, Vol. 76, No. 12, pp. 8189-8191.							
KC	VR	Khan et al., "Effects of Si On Photoluminescence of GaN", Solid State Communication, Vol. 57, No. 6, pp. 405-409, (1986).							
	WR	Matsushita et al., "PN Junction Type SiC Blue Light-Emitting Diodes", Applied Physics, Vol. 60, No. 2, pp. 159-162, Feb. 1991. <u>in Japanese only</u>							

Examiner

K. Chandra

Date Considered:

6/18/2002

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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**INFORMATION DISCLOSURE STATEMENT  
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	KR					
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	OR							
	PR							
	QR							
	RR							
	SR							
	TR							

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XC	UR	Goldenberg et al., "Ultraviolet and violet light-emitting GaN diodes grown by low-pressure metalorganic chemical vapor deposition". Applied Physics Letters 62 (1993) 25 January, No. 4, New York, New York				
XC	VR	Nakamura et al., "High-power InGaN/GaN double-heterostructure violet light emitting diodes," Applied Physics Letters, Vol. 62, No. 19, May 10, 1993, pp. 2390-2392.				
XC	WR	Patent Abstracts of Japan, Vol. 018, No. 080 (E-1505), February 9, 1994 & JP 05 291621 A (Nichia Chem Ind Ltd.), November 5, 1993.				
XC	XR	Patent Abstracts of Japan, Vol. 018, No. 507 (E-1609), September 22, 1994 & JP 06 177434 A (Nichia Chem Ind Ltd.), June 24, 1994.				
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Examiner *XC*

Date Considered: 2/18/2002

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